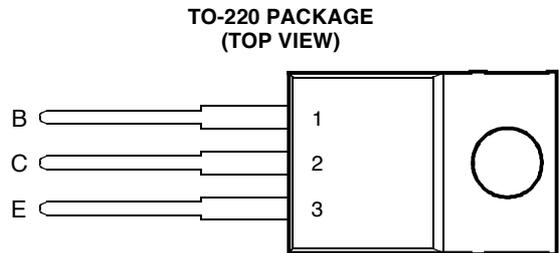


- Rugged Triple-Diffused Planar Construction
- 4 A Continuous Collector Current
- Operating Characteristics Fully Guaranteed at 100°C
- 1000 Volt Blocking Capability



This series is obsolete and not recommended for new designs.



Pin 2 is in electrical contact with the mounting base.

MDTRACA

**absolute maximum ratings at 25°C case temperature (unless otherwise noted)**

RATING		SYMBOL	VALUE	UNIT
Collector-base voltage ( $I_E = 0$ )	TIPL791	$V_{CBO}$	850	V
	TIPL791A		1000	
Collector-emitter voltage ( $V_{BE} = 0$ )	TIPL791	$V_{CES}$	850	V
	TIPL791A		1000	
Collector-emitter voltage ( $I_B = 0$ )	TIPL791	$V_{CEO}$	400	V
	TIPL791A		450	
Emitter-base voltage		$V_{EBO}$	10	V
Continuous collector current		$I_C$	4	A
Peak collector current (see Note 1)		$I_{CM}$	8	A
Continuous device dissipation at (or below) 25°C case temperature		$P_{tot}$	75	W
Operating junction temperature range		$T_j$	-65 to +150	°C
Storage temperature range		$T_{stg}$	-65 to +150	°C

NOTE 1: This value applies for  $t_p \leq 10$  ms, duty cycle  $\leq 2\%$ .

**PRODUCT INFORMATION**

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**electrical characteristics at 25°C case temperature (unless otherwise noted)**

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
$V_{CE(sus)}$ Collector-emitter sustaining voltage	$I_C = 100\text{ mA}$ $L = 25\text{ mH}$ (see Note 2) TIPL791 TIPL791A	400 450			V
$I_{CES}$ Collector-emitter cut-off current	$V_{CE} = 850\text{ V}$ $V_{BE} = 0$ $V_{CE} = 1000\text{ V}$ $V_{BE} = 0$ $V_{CE} = 850\text{ V}$ $V_{BE} = 0$ $T_C = 100^\circ\text{C}$ $V_{CE} = 1000\text{ V}$ $V_{BE} = 0$ $T_C = 100^\circ\text{C}$			5 5 200 200	$\mu\text{A}$
$I_{CEO}$ Collector cut-off current	$V_{CE} = 400\text{ V}$ $I_B = 0$ $V_{CE} = 450\text{ V}$ $I_B = 0$			5 5	$\mu\text{A}$
$I_{EBO}$ Emitter cut-off current	$V_{EB} = 10\text{ V}$ $I_C = 0$			1	mA
$h_{FE}$ Forward current transfer ratio	$V_{CE} = 5\text{ V}$ $I_C = 0.5\text{ A}$ (see Notes 3 and 4)	20		60	
$V_{CE(sat)}$ Collector-emitter saturation voltage	$I_B = 0.2\text{ A}$ $I_C = 1\text{ A}$ $I_B = 0.5\text{ A}$ $I_C = 2.5\text{ A}$ (see Notes 3 and 4) $I_B = 1\text{ A}$ $I_C = 4\text{ A}$ $I_B = 1\text{ A}$ $I_C = 4\text{ A}$ $T_C = 100^\circ\text{C}$			0.5 1.0 2.5 5.0	V
$V_{BE(sat)}$ Base-emitter saturation voltage	$I_B = 0.2\text{ A}$ $I_C = 1\text{ A}$ $I_B = 0.5\text{ A}$ $I_C = 2.5\text{ A}$ (see Notes 3 and 4) $I_B = 1\text{ A}$ $I_C = 4\text{ A}$ $I_B = 1\text{ A}$ $I_C = 4\text{ A}$ $T_C = 100^\circ\text{C}$			1.0 1.2 1.4 1.3	V
$f_t$ Current gain bandwidth product	$V_{CE} = 10\text{ V}$ $I_C = 0.5\text{ A}$ $f = 1\text{ MHz}$		12		MHz
$C_{ob}$ Output capacitance	$V_{CB} = 20\text{ V}$ $I_E = 0$ $f = 0.1\text{ MHz}$		110		pF

- NOTES: 2. Inductive loop switching measurement.  
3. These parameters must be measured using pulse techniques,  $t_p = 300\ \mu\text{s}$ , duty cycle  $\leq 2\%$ .  
4. These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.

**thermal characteristics**

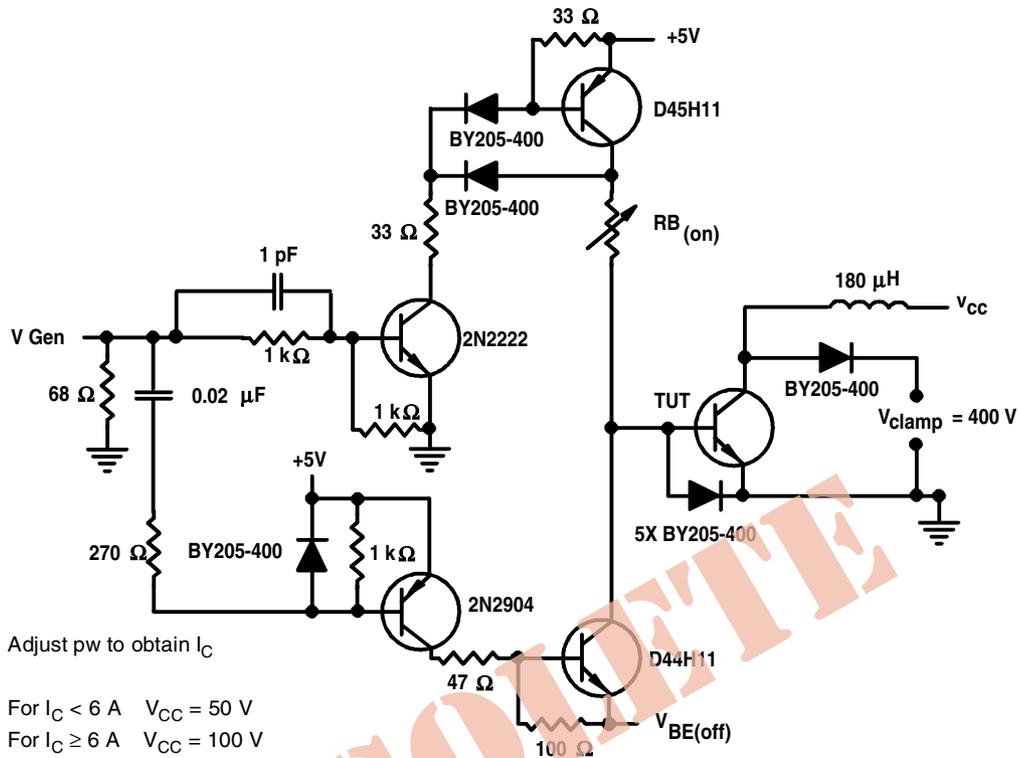
PARAMETER	MIN	TYP	MAX	UNIT
$R_{\theta JC}$ Junction to case thermal resistance			1.66	$^\circ\text{C/W}$

**inductive-load-switching characteristics at 25°C case temperature (unless otherwise noted)**

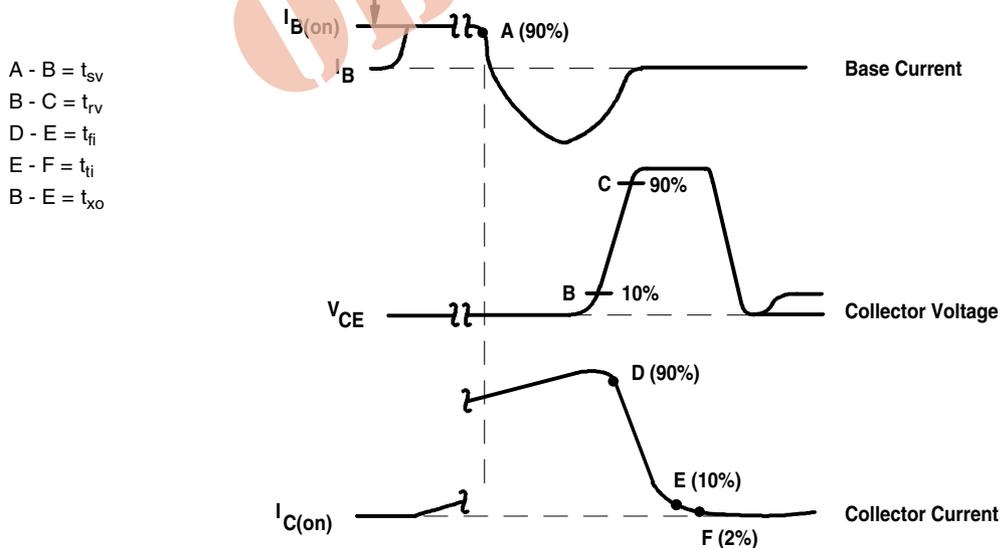
PARAMETER	TEST CONDITIONS †	MIN	TYP	MAX	UNIT
$t_{sv}$ Voltage storage time	$I_C = 4\text{ A}$ $I_{B(on)} = 0.8\text{ A}$ (see Figures 1 and 2) $V_{BE(off)} = -5\text{ V}$			2	$\mu\text{s}$
$t_{rv}$ Voltage rise time				200	ns
$t_{fi}$ Current fall time				100	ns
$t_{ti}$ Current tail time				50	ns
$t_{xo}$ Cross over time				200	ns
$t_{sv}$ Voltage storage time	$I_C = 4\text{ A}$ $I_{B(on)} = 0.8\text{ A}$ (see Figures 1 and 2) $V_{BE(off)} = -5\text{ V}$ $T_C = 100^\circ\text{C}$			2.5	$\mu\text{s}$
$t_{rv}$ Voltage rise time				400	ns
$t_{fi}$ Current fall time				200	ns
$t_{ti}$ Current tail time				50	ns
$t_{xo}$ Cross over time				600	ns

† Voltage and current values shown are nominal; exact values vary slightly with transistor parameters.

**PARAMETER MEASUREMENT INFORMATION**



**Figure 1. Inductive-Load Switching Test Circuit**



NOTES: A. Waveforms are monitored on an oscilloscope with the following characteristics:  $t_r < 15 \text{ ns}$ ,  $R_{in} > 10 \Omega$ ,  $C_{in} < 11.5 \text{ pF}$ .  
 B. Resistors must be noninductive types.

**Figure 2. Inductive-Load Switching Waveforms**

**PRODUCT INFORMATION**

TYPICAL CHARACTERISTICS

TYPICAL DC CURRENT GAIN  
VS  
COLLECTOR CURRENT

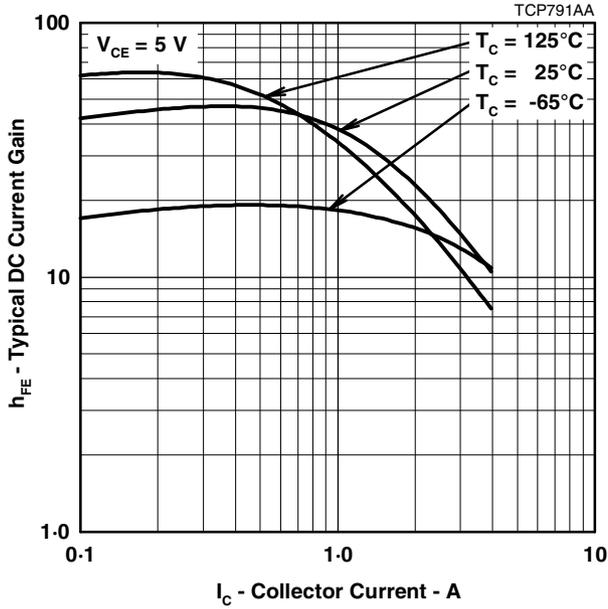


Figure 3.

COLLECTOR-EMITTER SATURATION VOLTAGE  
VS  
BASE CURRENT

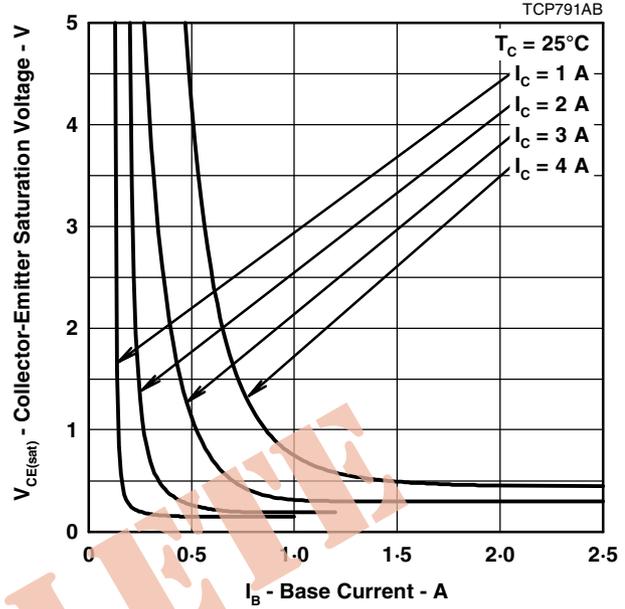


Figure 4.

MAXIMUM SAFE OPERATING REGIONS

MAXIMUM FORWARD-BIAS  
SAFE OPERATING AREA

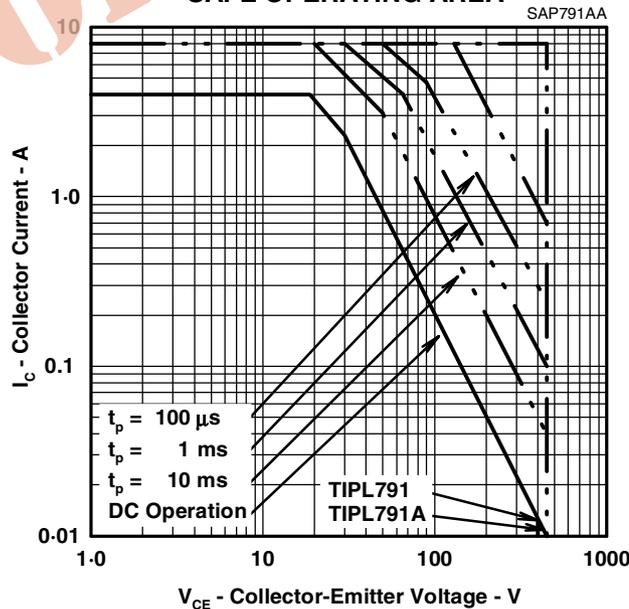


Figure 5.

**PRODUCT INFORMATION**

**THERMAL INFORMATION**

**THERMAL RESPONSE JUNCTION TO CASE  
VS  
POWER PULSE DURATION**

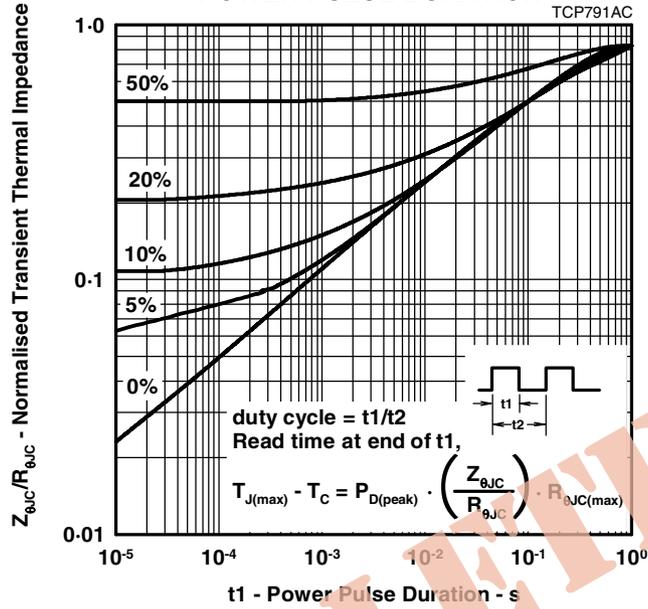


Figure 6.

**PRODUCT INFORMATION**

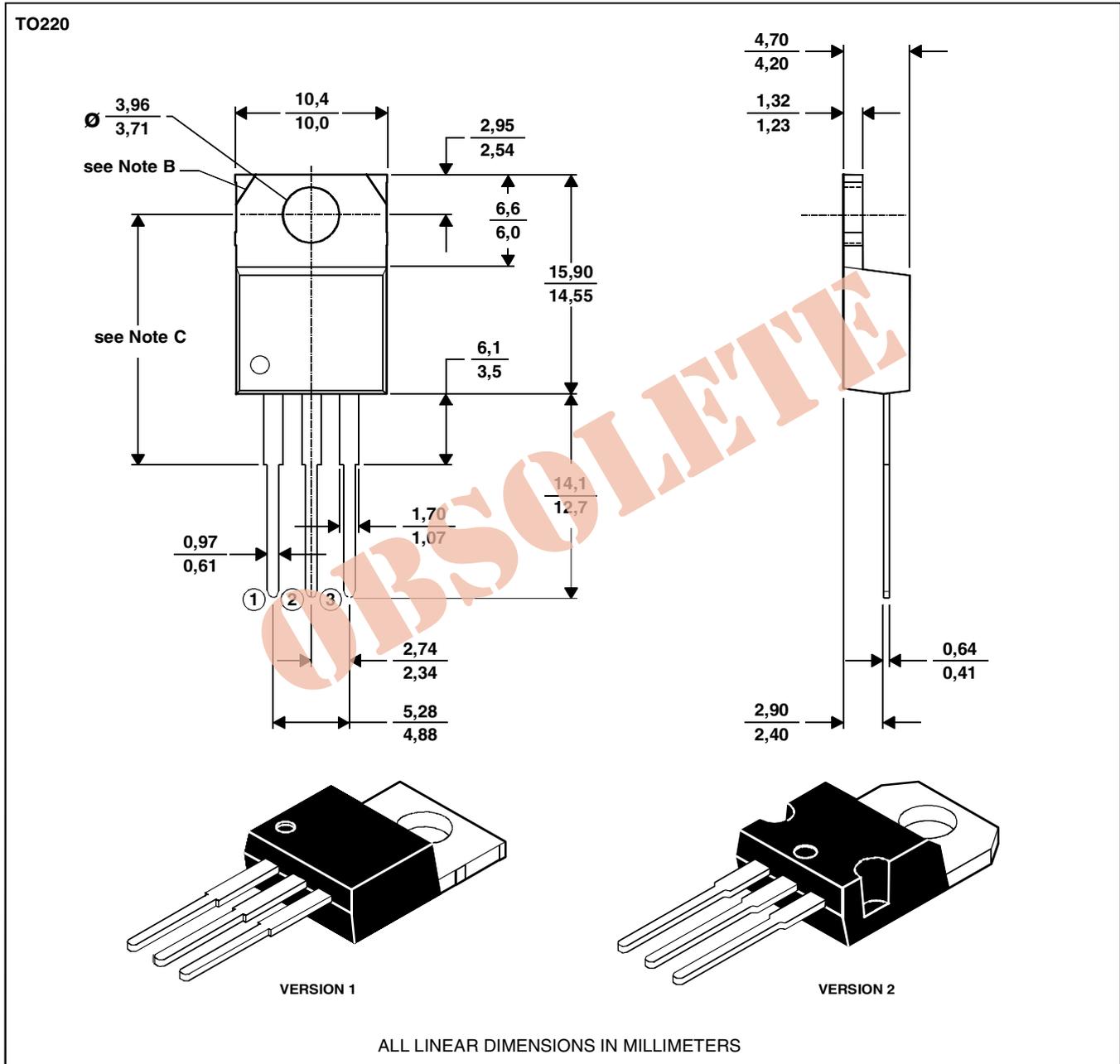
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**MECHANICAL DATA**

**TO-220**

**3-pin plastic flange-mount package**

This single-in-line package consists of a circuit mounted on a lead frame and encapsulated within a plastic compound. The compound will withstand soldering temperature with no deformation, and circuit performance characteristics will remain stable when operated in high humidity conditions. Leads require no additional cleaning or processing when used in soldered assembly.



NOTES: A. The centre pin is in electrical contact with the mounting tab.  
 B. Mounting tab corner profile according to package version.  
 C. Typical fixing hole centre stand off height according to package version.  
 Version 1, 18.0 mm. Version 2, 17.6 mm.

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